

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 11-214656

(43)Date of publication of application : 06.08.1999

(51)Int.Cl.

H01L 27/108
H01L 21/8242
H01L 21/8234
H01L 27/088

(21)Application number : 10-017232

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(22)Date of filing : 29.01.1998

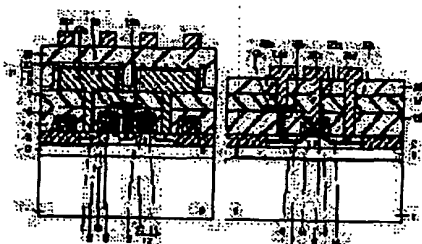
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(54) SEMICONDUCTOR DEVICE AND MANUFACTURE THEREOF

(57)Abstract:

PROBLEM TO BE SOLVED: To lower the concn. of an impurity region for controlling the threshold voltage of a first transistor to enable the junction leakage current reduction, by making thicker a gate insulation film of the first transistor than that of a second transistor.

SOLUTION: A gate electrode 12 is formed through a gate insulation film 8 in a memory cell on a main surface of a p-type semiconductor substrate 1 sandwiched between source-drain regions, a gate electrode 12 is formed through a gate insulation film 9 in a peripheral circuit, the thickness of the gate insulation film 8 in the memory cell is set to be greater than that of the gate insulation film 9 in the peripheral circuit to thereby enable the concn. reduction at a p-type impurity region 4a in the memory cell. By lowering the concn. at the p-type impurity region 4a, the junction leak current can be reduced.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]